

## **PN2484**

## **MMBT2484**





## **NPN General Purpose Amplifier**

This device is designed for low noise, high gain, general purpose amplifier applications at collector currents from  $1\mu$  to 50 mA. Sourced from Process 07. See 2N5088 for characteristics.

## **Absolute Maximum Ratings\***

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CEO}$	Collector-Emitter Voltage	60	V
V <sub>CBO</sub>	Collector-Base Voltage	60	V
V <sub>EBO</sub>	Emitter-Base Voltage	5.0	V
Ic	Collector Current - Continuous	100	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

- These ratings are based on a maximum junction temperature of 150 degrees C.
   These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

### **Thermal Characteristics**

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max		Units	
		PN2484	*MMBT2484		
$P_D$	Total Device Dissipation	625	350	mW	
	Derate above 25°C	5.0	2.8	mW/°C	
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3		°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	°C/W	

<sup>\*</sup>Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

## **NPN General Purpose Amplifier**

(continued)

## **Electrical Characteristics**

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
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$BV_{CBO}$	Collector-Base Breakdown Voltage	$I_C = 10  \mu A, I_B = 0$	60		V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage*	$I_C = 10 \text{ mA}, I_E = 0$	60		V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_C = 10 \mu A, I_E = 0$	6.0		V
I <sub>CBO</sub>	Collector Cutoff Current	$V_{CB} = 45 \text{ V}, I_{E} = 0$		10	nA
		$V_{CB} = 45 \text{ V}, I_E = 0, T_A = 150^{\circ}\text{C}$		10	μΑ
I <sub>EBO</sub>	Emitter Cutoff Current	$V_{EB} = 5.0 \text{ V}, I_{C} = 0$		10	nA

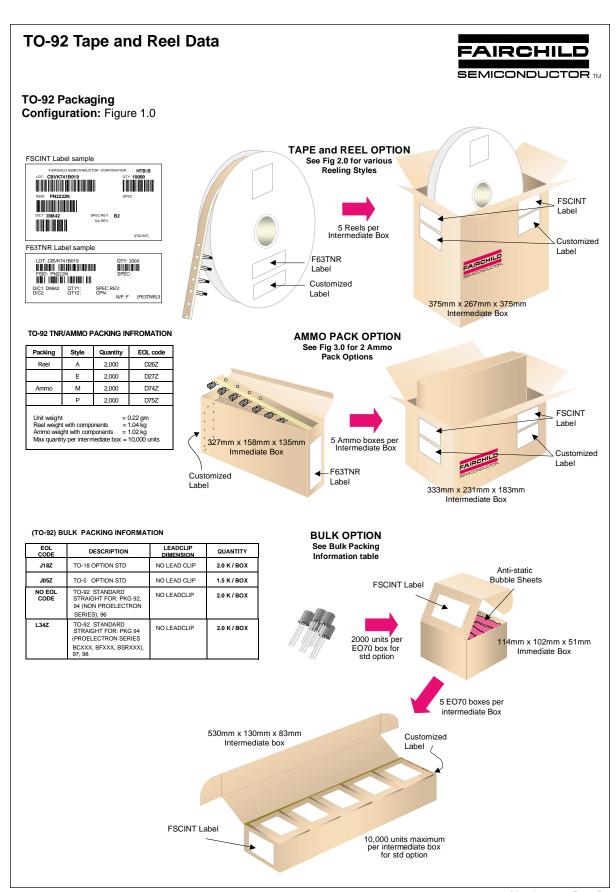
#### **ON CHARACTERISTICS**

h <sub>FE</sub>	DC Current Gain	$\begin{split} I_C &= 1.0 \ \mu\text{A}, \ V_{CE} = 5.0 \ V \\ I_C &= 10 \ \mu\text{A}, \ V_{CE} = 5.0 \ V \\ I_C &= 100 \ \mu\text{A}, \ V_{CE} = 5.0 \ V \\ I_C &= 100 \ \mu\text{A}, \ V_{CE} = 5.0 \ V \\ T_A &= -55^{\circ}\text{C} \\ I_C &= 500 \ \mu\text{A}, \ V_{CE} = 5.0 \ V \\ I_C &= 1.0 \ \text{mA}, \ V_{CE} = 5.0 \ V \\ I_C &= 10 \ \text{mA}, \ V_{CE} = 5.0 \ V \end{split}$	30 100 175 20 200 250	500 800	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_C = 1.0 \text{ mA}, I_B = 0.1 \text{ mA}$		0.35	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	$I_C = 100 \mu\text{A},  V_{CE} = 5.0 \text{V}$	0.5	0.7	V

## SMALL SIGNAL CHARACTERISTICS

$C_{obo}$	Output Capacitance	V <sub>CB</sub> =5.0 V, f = 140 kHz	6.0	pF
C <sub>ibo</sub>	Input Capacitance	V <sub>EB</sub> = 0.5 V, f = 140 kHz	6.0	pF
NF	Noise Figure	$I_C = 10 \mu A$ , $V_{CE} = 5.0 \text{ V}$ , $R_S = 10 \text{k,f} = 1.0 \text{ kHz,BW} = 200 \text{ Hz}$	3.0	dB

<sup>\*</sup>Pulse Test: Pulse Width  $\leq\!300~\mu\text{s},$  Duty Cycle  $\leq\!3.0\%$ 

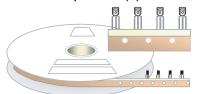


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## TO-92 Tape and Reel Data and Package Dimensions, continued

# **TO-92 Reeling Style Configuration:** Figure 2.0

#### Machine Option "A" (H)

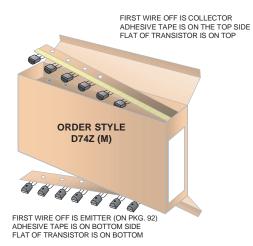


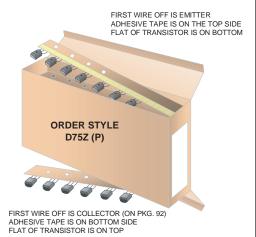
Style "A", D26Z, D70Z (s/h)

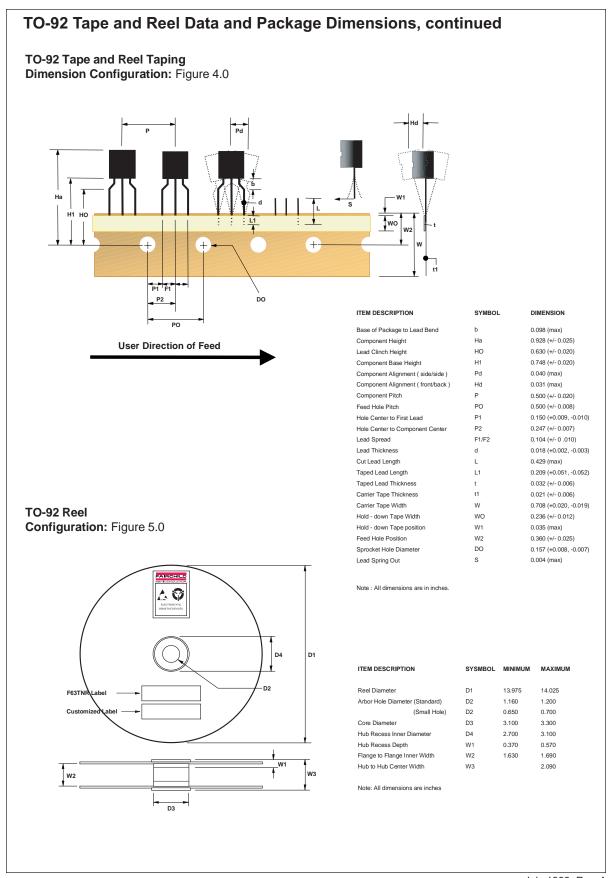
# Machine Option "E" (J)

Style "E", D27Z, D71Z (s/h)

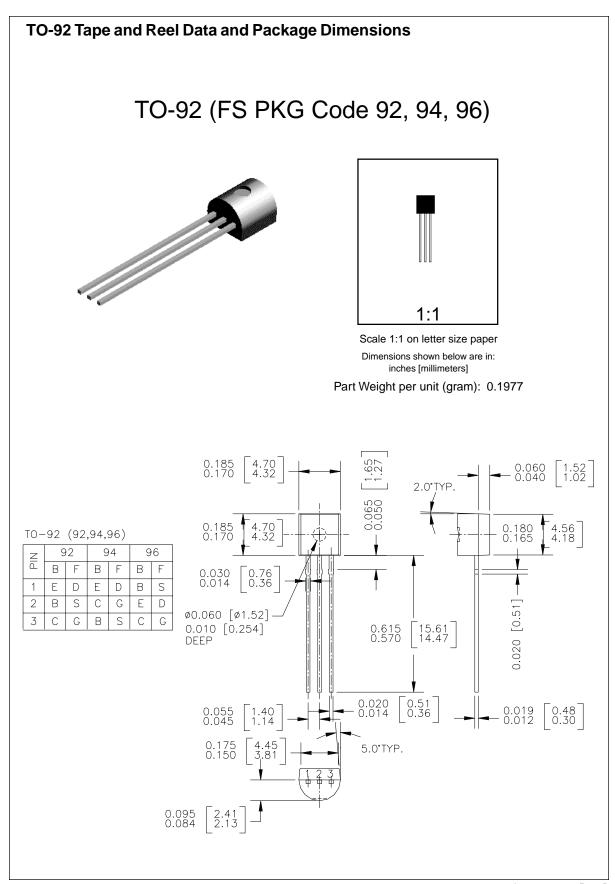
## **TO-92 Radial Ammo Packaging Configuration:** Figure 3.0







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January 2000, Rev. B

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Rev. G